

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION

Please replace the paragraph [0167] with the following amended paragraph:

In s a thirteenth embodiment, nanometer-size conductive particles fabricated by the particle forming method of the present invention are formed in an insulator on a semiconductor substrate, and an electrode is further formed on the insulator by an ordinary method. A substance that has electrical conductivity, such as a metal or polysilicon, can be employed for the electrode. Then, source and drain regions are formed in the semiconductor substrate by a method used for flash memory or other conventional transistors to constitute a field-effect type transistor. In this way, s a memory device of the present invention is completed.